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TRANSMITTAL	
FORM	

(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission

the date shown below:

Typed or printed name

Terri Lynn Foyd-Davis

Signature

Application Number 10/630,114 Certificate Filing Date July 29, 2003 First Named Inventor Charles H. Dennison Art Unit 2823 of Correction **Examiner Name** Lalrinfamkim Hmar Malsawma Attorney Docket Number MI22-2346

ENCLOSURES (Check all that apply)								
	Fee Tran	smittal Form		Drawing(s)			After Allowance Communication to TC Appeal Communication to Board	
	F∈	ee Attached		Licensing-related Papers			of Appeals and Interferences	
	Amendme	ent/Reply fter Final		Petition Petition to Convert to a Provisional Application			Appeal Communication to TC (Appeal Notice, Brief, Reply Brief) Proprietary Information	
		ffidavits/declaration(s)		Power of Attorney, Revocation Change of Correspondence			Status Letter Other Enclosure(s) (please Identify	
		n of Time Request Abandonment Request	片	Terminal Disclaimer Request for Refund		Retu	below): im Receipt Postcard; Request for	
	•	on Disclosure Statement		CD, Number of CD(s)		ificate of Correction; Certificate of rection (2)		
Certified Copy of Priority Document(s) Reply to Missing Parts/ Incomplete Application Reply to Missing Parts under 37 CFR 1.52 or 1.53		Landscape Table on CD Remarks Customer No. 021567 Patent No. 6,897,542 B2 Issued: May 24, 2005 No Fee Required. However, should a fee be de Deposit Account No. 23-0925.			etermined as owing, charge such a fee to			
		SIGNA	TURE	OF APPLICANT, ATTO	ORNEY, C	R AG	ENT	
Firm N	lame	Wells St. John, P.S.				_	Ą.	
Signat	ture	ch		-				
	d name	David G. Latwesen, Ph.D.						
Date //24/06		1/24/06			Reg. No.	38,533	3	
CERTIFICATE OF TRANSMISSION/MAILING								

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on

-24-06

Date

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No. 6,897,542 B2
Ratent Issue Date May 24, 2005
Application Serial No. 10/630,114
Filing Date July 29, 2003
Assignee Micron Technology, Inc.
Inventorship Charles H. Dennison
Attorney's Docket No. MI22-2346

Title: "Semiconductor Assemblies"

REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR PTO MISTAKE (37 C.F.R. 1.322(a))

To:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

ATTN:

Decision and Certificate of Correction

Branch of the Patent Issue Division

From:

David G. Latwesen, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 6,897,542 B2, granted May 24, 2005, in accordance with the Certificate of Correction form attached hereto in duplicate.

The errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Since this Certificate of Correction is being requested due to PTO errors, it is believed that no fee is due. However, in the event that a fee is required for issuance of this Certificate of Correction, please charge the fee specified under

01/27/2006 EAREGAY1 00000007 230925 10630114

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37 C.F.R. § 1.20(a) to Deposit Account No. 23-0925. Please credit Deposit Account No. 23-0925 with any overpayment of the above fee.

Attached hereto, in duplicate is Form PTO-1050, with at least one copy being suitable for printing.

Dated: 17/106

Respectfully submitted,

By:

David G. Latwesen, Ph.D.

Reg. No. 38,533

UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

Page 1 of 1

PATENT NO.

: US 6,897,542 B2

APPLICATION NO.: 10/630,114

DATED

: July 29, 2003

INVENTOR(S)

: Charles H. Dennison

It is certified that an error or errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On title page, item 56 References Cited, line 11 -Replace "6,097,677 A 8/2000 Wu" With --6,087,677 A 7/2000 Wu--

Col. 3, line 26 -

Replace "nitride (Si₃N) or silicon oxynitride (Si_xO_yN_z, wherein x, y" With --nitride (Si₃N₄) or silicon oxynitride (Si_xO_vN_z, wherein x, y--

Col. 6. line 36 -

Replace "throughto the first diffusion region and having a second" With --through to the first diffusion region and having a second--

Col. 8, line 16 -

Replace "with the planar uppermost surface. of the insulative" With --with the planar uppermost surface of the insulative--

Mailing Address of Sender:

David G. Latwesen, Ph.D. Wells St. John P.S. 601 West First Avenue, Suite 1300 Spokane, WA 99201-3828

Patent No. <u>US 6,897,542 B2</u>

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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